

12-Bit Low Power SAR ADC

NCD98010, NCD98011

The NCD98010 (unsigned output) and the NCD98011 (signed output) ADC products provide an extremely low power solution for analog to digital conversion applications using a capacitor-based successive-approximation architecture. Optimized for low power and speed, the NCD98010/1 can achieve a sample rate of 2 MSPS while consuming less than 1 mW of power. The device also features a large input voltage range of 1.65 V to 3.3 V for various applications for both analog and digital supplies. The SPI-compatible interface provides a straight-forward data-acquisition method.

Features

- Nanowatt Power Consumption
- Fully Differential Input
- 2-MSPS Throughput
- Small Package Size
- Pre-Calibrated
- SPI Interface
- These Devices are Pb-Free, Halogen Free/BFR Free and icesces a1T4 0

- Portable Medical Equipment
- Glucose Meters

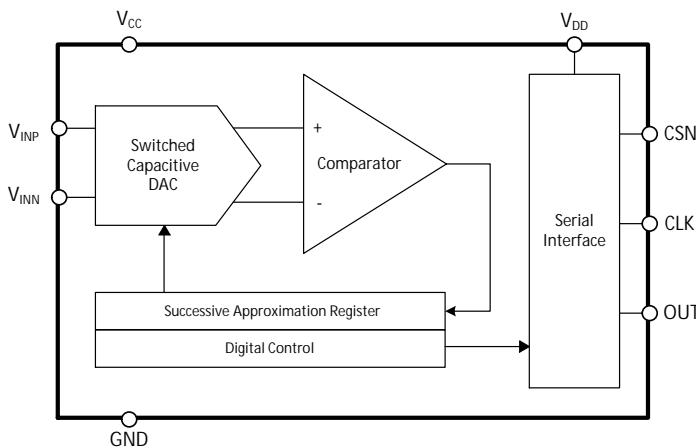
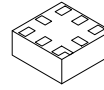
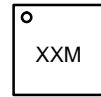


Figure 1. Block Diagram

MARKING DIAGRAMS

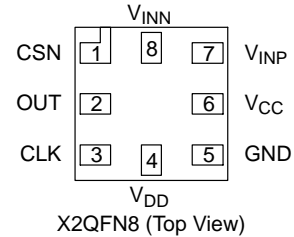


X2QFN8
DP SUFFIX
CASE 722AM



XX = Specific Device Code
M = Date Code

PIN CONFIGURATION



ORDERING INFORMATION

Device	Package	Shipping†
NCD98010XMXTAG	X2QFN	5000 / Tape & Reel
NCD98011XMXTAG		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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PIN DESCRIPTION

X2QFN Pin No.	Name	Function
1	CSN	Chip select (active low)
2	OUT	Data Output (serialized)
3	CLK	Clock
4	VDD	Digital I/O supply voltage
5	GND	Common ground for all pins
6	VCC	Analog supply and ADC reference voltage
7	V _{INP}	Analog input, positive signal
8	V _{INN}	Analog input, negative signal

MAXIMUM RATINGS

Rating	Symbol
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ELECTRICAL CHARACTERISTICS (T_J = 25°C, V_{CC} = 3 V, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ
POWER SUPPLY REQUIREMENTS				
Analog Supply and ADC reference		V _{CC}	1.65	3
Digital I/O Supply		V _{DD}	1.65	3
Analog Supply Current	2 MSPS for V _{CC} = 3.6 V	I _{VCC}		100
	1 MSPS for V _{CC} = 3 V			50
	100 kSPS for V _{CC} = 3.6 V			7
	1 MSPS for V _{CC} = 1.8 V			7
Analog Power Dissipation	2 MSPS for V _{CC} = 3.6 V	P _{VCC}		
	1 MSPS for V _{CC} = 3 V			
	100 kSPS for V _{CC} = 3.6 V			
	1 MSPS for V _{CC} = 1.8 V			
Digital Supply Current Dependent on SDO loading (tested with ~7 pF)	2 MSPS for V _{DD} = 3.6 V	I _{VDD}		
	1 MSPS for V _{DD} = 3 V			
	100 kSPS for V _{DD} = 3.6 V			
	1 MSPS for V _{DD} = 1.8 V			
Standby current (CSN high) (Note 2)	V _{CC} = 3.6 V	I _{STNDBY}		

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ELECTRICAL CHARACTERISTICS (T_J = 25°C, V_{CC} = 3 V, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS						
Total-Harmonic Distortion	f _{IN} = 1 kHz V _{CC} = 3.3 V	THD		-80		dB
	f _{IN} = 1 kHz V _{CC} = 1.8 V			-80		
Signal-to-Noise and Distortion (Note 4)	f _{IN} = 1 kHz V _{CC} = 3.3 V	SINAD	68	69		dB
	f _{IN} = 1 kHz V _{CC} = 1.8 V			62		
Spurious-Free Dynamic Range (Note 4)	f _{IN} = 1 kHz V _{CC} = 3.3 V	SFDR	69	80		dB
	f _{IN} = 1 kHz V _{CC} = 1.8 V			74		

DIGITAL INPUT/OUTPUT

High-Level Input Voltage		V _{IH}	V _{DD} *0.7			V
Low-Level Input Voltage		V _{IL}			V _{DD} *0.3	V
High-Level Output Voltage	2 mA drive	V _{OH}	V _{DD} - 0.5 V			V
Low-Level Output Voltage	2 mA drive	V _{OL}			GND+0.5	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Standby current includes both digital and analog currents.
3. INL and DNL parameters were verified via bench testing and are not used for production screening.
4. SINAD and SFDR are tested at production and guaranteed by correlation to bench test results.

TIMING CHARACTERISTICS (T_J = 25°C unless otherwise specified)

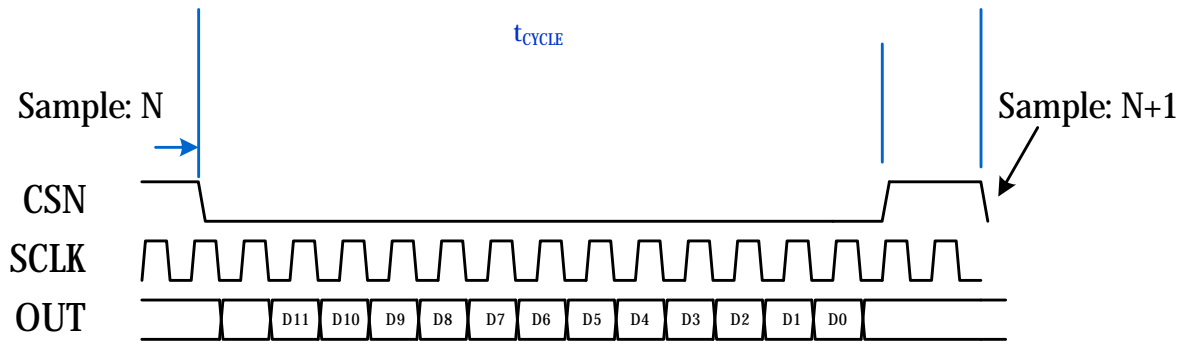
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
TIMING SPECIFICATIONS						
Throughput		f _{THROUGH}			2	MSPS
Cycle Time		f _{CYCLE}	0.5			μs
Conversion Time		f _{CONV}	437.5			ns
Data Delay				1		cycle

TIMING REQUIREMENTS

Acquisition Time (CSN high)		t _{ACQ}	62.5			ns
CLK Frequency		f _{CLK}			32	MHz
CLK Period		t _{CLK}			31.25	ns
CSN Falling to 1 st SCLK falling edge		t _{CSN_SCLK}	15.75			ns
Last SCLK falling edge to CSN rising		t _{SCLK_CSN}	15.75			ns
Falling SCLK to SDO valid (Note 5)	Assumed 10 pF Load	t _{SDO_VALID}			30	ns

5. When SCLK is running at higher frequencies, the t_{SDO_VALID} of 30 ns requires SDO to be sampled on the falling edge of SCLK at the end of the bit width just before SDO changes to the next output. This will ensure acquisition of the correct data. For example, location A shown below would be the best place to sample SDO for the acquisition of bit 9.

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Data: N-1

Figure 2. Serial Interface Timing

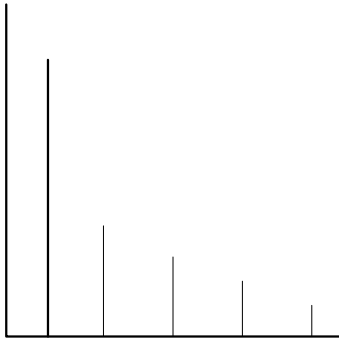


Figure 16. Spurious Free Dynamic Range in the Frequency Domain

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1 μ F. All decoupling capacitors must connect directly to a low impedance ground plane in order to be effective. Short traces or vias are required to minimize additional series inductance. Ceramic capacitors are recommended based on their low ESR and ESL. X7R ceramic capacitors are recommended for applications involving a wide temperature range.

Minimal Component Realization

For applications where minimizing board space trumps ADC performance, the NCD98010/1 connection diagram can be reduced as shown in Figure 21 below. The removal of the input buffering may be an option depending on the nature of the differential analog input source. Removing the anti-aliasing filter would come at the expense of reduced ENOB due to the digitization of aliased signals.

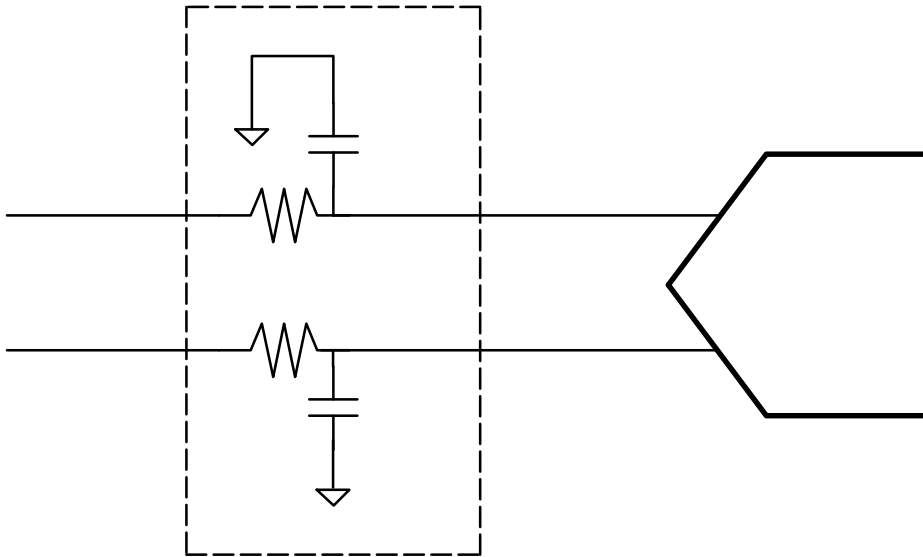


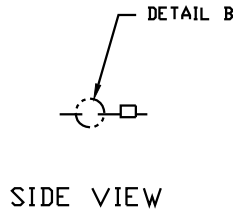
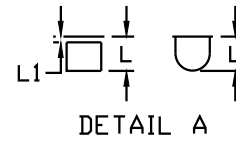
Figure 21. Reduced Component Connection Diagram

X2QFN8, 1.5x1.5, 0.5P
CASE 722AM
ISSUE O

DATE 20 JUL 2018



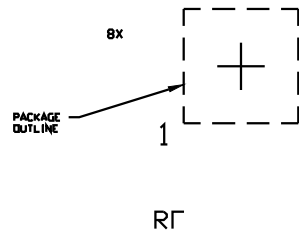
COPLAN



DETAIL B

7x

BOTTOM VIEW



GENERIC MARKING DIAGRAM*

- X = Specific Device Code
- M = Date Code
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*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



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